NSN 5961-00-166-3917

Photo Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-00-166-3917 **Inclosure Material:** Metal and glass **Overall Length:** Between 0.170 inches and 0.210 inches **Terminal Length:** 0.500 inches **Overall Diameter:** Between 0.209 inches and 0.230 inches **Function For Which Designed:** Detector **Internal Configuration:** Junction contact **Mounting Method: Terminal Terminal Circle Diameter:** Between 0.090 inches and 0.110 inches **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 40.0 reverse voltage, dc **Current Rating Per Characteristic:** 3.00 milliamperes collector cutoff current, dc, emitter open and 25.00 nanoamperes repetitive peak forward current peak **Power Rating Per Characteristic:** 75.0 milliwatts small-signal input power, common-collector preset **Maximum Operating Tempurature Per Measurement Point:** 125.0 degrees celsius ambient air **Special Features:** Junction pattern arrangement: npn **Terminal Type And Quantity:** 3 uninsulated wire lead Shelf Life: N/a **Unit Of Measure: Demilitarization:**

Yes - demil/mli

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